Seminar

Institute for Plasma Research

Title: Precursor Material for High Temperature

Application

Speaker: Dr. Arvind Saxena

Director, Defence Materials Research &

Development Establishment (DMSRDE), Kanpur

Date: 11th June 2015 (Thursday)

Time: 11.00 AM

Venue: Committee Room 4 (New Building), IPR

Abstract:

The talk will aim at precursor material developed for SiC i.e., Polycarbosilane and how it has been used for making SiC fibers. Areas like CFCMCs using PIP process, CMCs, Refractory material, magnetic material, ablative liner, coating of CNT to make electrical conducting but thermal insulating FRPs, SiC thin films for semiconductor application using MO CVD, Plasma CVD techniques etc will be discussed.